



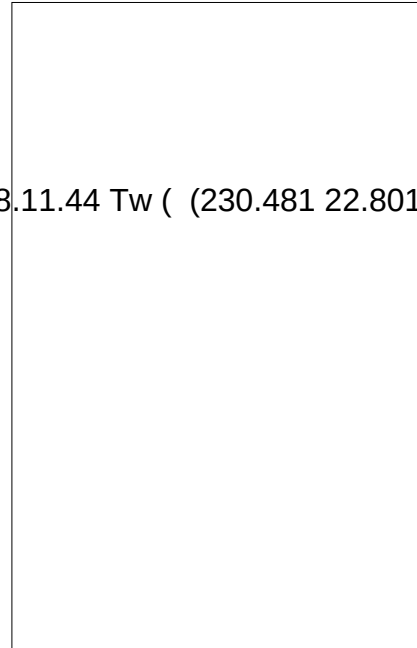
JCT816EH 20A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT816EH SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for

UnitUnitUnitU91.679 0.48 re f 458.52 [(U91.679 0.48.11.44 Tw ((230.481 22.801 re f <</MC



ORDERING INFORMATION

J	CT	8	16	E	H	-/
JieJie Microelectronics Co., Ltd.	SCRs					Blank:Tube -TR:Tape & Reel
	8:V _{DRM} /V _{RRM} 800V		I _{T(RMS)} :16A	E:TO-263	High junction temperature	

MARKING

FIG.1: Maximum power dissipation versus RMS on-state current

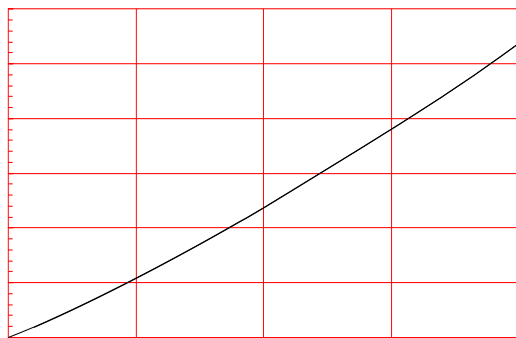
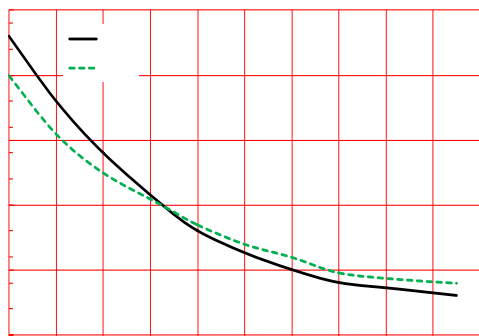


FIG.2: RMS on-state current versus case temperature

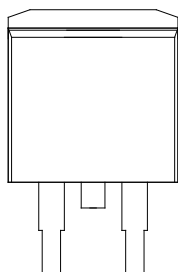
FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



JCT816EH

JieJie M d [(EMT0 E T28498)0 15.71.16

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

